## Moritz Heintze

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

1,284 43 21 35 h-index g-index citations papers 46 1,338 3.96 3.7 L-index avg, IF ext. papers ext. citations

#	Paper	IF	Citations
43	Power supply efficiency in dual magnetron large area sputter coatings. <i>Plasma Research Express</i> , <b>2020</b> , 2, 035006	1	
42	Nodule formation on sputtering targets: Causes and their control by MF power supplies. <i>Surface and Coatings Technology</i> , <b>2018</b> , 336, 80-83	4.4	5
41	Hydrogen and Syngas Production from Hydrocarbons <b>2012</b> , 353-391		1
40	Methane oxidation in a dielectric barrier discharge. the impact of discharge power and discharge gap filling. <i>Reaction Kinetics and Catalysis Letters</i> , <b>2004</b> , 82, 111-119		5
39	The impact of a dielectric barrier discharge on the catalytic oxidation of methane over Ni-containing catalyst. <i>Reaction Kinetics and Catalysis Letters</i> , <b>2004</b> , 82, 131-137		14
38	Plasma catalytic conversion of methane into syngas: the combined effect of discharge activation and catalysis. <i>Catalysis Today</i> , <b>2004</b> , 89, 21-25	5.3	73
37	Methane conversion at low temperature: the combined application of catalysis and non-equilibrium plasma. <i>Catalysis Today</i> , <b>2004</b> , 90, 151-158	5.3	75
36	Plasma-assisted partial oxidation of methane to synthesis gas in a dielectric barrier discharge. <i>Applied Catalysis A: General</i> , <b>2004</b> , 261, 19-24	5.1	52
35	Surface modification of carbon nanofibres in low temperature plasmas. <i>Diamond and Related Materials</i> , <b>2004</b> , 13, 1177-1181	3.5	44
34	Analysis of functional groups on the surface of plasma-treated carbon nanofibers. <i>Analytical and Bioanalytical Chemistry</i> , <b>2003</b> , 375, 875-83	4.4	24
33	Surface functionalisation of carbon nano-fibres in fluidised bed plasma. <i>Surface and Coatings Technology</i> , <b>2003</b> , 174-175, 831-834	4.4	12
32	Characterization of the uppermost layer of plasma-treated carbon nanotubes. <i>Diamond and Related Materials</i> , <b>2003</b> , 12, 811-815	3.5	108
31	Basic analytical investigation of plasma-chemically modified carbon fibers. <i>Spectrochimica Acta, Part B: Atomic Spectroscopy</i> , <b>2002</b> , 57, 1601-1610	3.1	82
30	Methane Conversion into Aromatics in a Direct Plasma-Catalytic Process. <i>Journal of Catalysis</i> , <b>2002</b> , 206, 91-97	7.3	32
29	Mechanism of C2 hydrocarbon formation from methane in a pulsed microwave plasma. <i>Journal of Applied Physics</i> , <b>2002</b> , 92, 7022-7031	2.5	87
28	Methane conversion into acetylene in a microwave plasma: Optimization of the operating parameters. <i>Journal of Applied Physics</i> , <b>2002</b> , 92, 2276-2283	2.5	49
27	Versatile High Rate Plasma Deposition and Processing with very high Frequency Excitation.  Materials Research Society Symposia Proceedings, 1997, 467, 471		8

26	Properties of amorphous boron nitride thin films. Journal of Non-Crystalline Solids, 1996, 198-200, 403-4	10,69	41
25	New diagnostic aspects of high rate a-Si:H deposition in a VHF plasma. <i>Journal of Non-Crystalline Solids</i> , <b>1996</b> , 198-200, 1038-1041	3.9	37
24	Laser induced nucleation and growth of polycrystalline silicon. <i>Journal of Non-Crystalline Solids</i> , <b>1996</b> , 198-200, 887-890	3.9	7
23	The Effect of Hydrogen Dilution on the Hot-Wire Deposition of Microcrystalline Silicon. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 420, 295		10
22	Highly Conductive p-type Microcrystalline Silicon Thin Films. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 420, 277		3
21	Charge Carrier Absorption in Doped Microcrystalline Silicon Films. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 452, 815		
20	Substrate selective deposition and etching of silicon thin films. <i>Journal of Applied Physics</i> , <b>1995</b> , 77, 879	-884	17
19	Detection of SiH2radicals in an a-Si:H deposition plasma by laser-induced fluorescence. <i>Journal Physics D: Applied Physics</i> , <b>1995</b> , 28, 2470-2472	3	1
18	Lateral structuring of silicon thin films by interference crystallization. <i>Applied Physics Letters</i> , <b>1994</b> , 64, 3148-3150	3.4	49
17	Microcrystalline Silicon Thin film Growth and Simultaneous Etching of Amorphous Material. <i>Materials Research Society Symposia Proceedings</i> , <b>1994</b> , 358, 733		1
16	Control of a-Si:H deposition by the ion flux in a VHF plasma. <i>Journal of Non-Crystalline Solids</i> , <b>1993</b> , 164-166, 55-58	3.9	28
15	Deposition of a-Si:H with the hot-wire technique. <i>Journal of Non-Crystalline Solids</i> , <b>1993</b> , 164-166, 83-86	3.9	33
14	Surface controlled plasma deposition and etching of silicon near the chemical equilibrium. <i>Journal of Non-Crystalline Solids</i> , <b>1993</b> , 164-166, 985-988	3.9	31
13	Amorphous hydrogenated silicon carbon from VHF deposition. <i>Journal of Non-Crystalline Solids</i> , <b>1993</b> , 164-166, 1031-1034	3.9	5
12	Analysis of high-rate a-Si:H deposition in a VHF plasma. <i>Journal Physics D: Applied Physics</i> , <b>1993</b> , 26, 178	1 <sub>3</sub> 1786	<b>5</b> 76
11	An Approach to High Quality a-Ge:H by VHF Deposition. <i>Materials Research Society Symposia Proceedings</i> , <b>1993</b> , 297, 55		3
10	Analysis of VHF Glow Discharge of A-SI:H Over a Wide Frequency Range. <i>Materials Research Society Symposia Proceedings</i> , <b>1992</b> , 258, 147		9
9	Infrared spectroscopy during hydrogen effusion of a-Si:H, a-SiGe:H and a-Ge:H. <i>Journal of Non-Crystalline Solids</i> , <b>1991</b> , 137-138, 49-52	3.9	11

8	Thermally induced changes of conductivity in undoped and doped amorphous germanium. <i>Journal of Non-Crystalline Solids</i> , <b>1991</b> , 137-138, 187-190	3.9	8
7	The mechanism of plasma-induced deposition of amorphous silicon from silane. <i>Plasma Chemistry and Plasma Processing</i> , <b>1990</b> , 10, 3-26	3.6	67
6	Development of plasma CVD and feasibility study of boron carbide in-situ coatings for tokamaks. Journal of Nuclear Materials, <b>1989</b> , 162-164, 724-731	3.3	57
5	Role of higher silanes in the plasma-induced deposition of amorphous silicon from silane. <i>Applied Physics Letters</i> , <b>1989</b> , 54, 1320-1322	3.4	16
4	From the Understanding of the Reaction Mechanism Towards Optimizing the Deposition Rate and Optoelectronic Properties of a-Si:H. <i>Materials Research Society Symposia Proceedings</i> , <b>1989</b> , 149, 3		6
3	Mechanisms of Plasma Induced Silicon Deposition and the Control of the Properties of the Deposit. <i>Materials Research Society Symposia Proceedings</i> , <b>1988</b> , 118, 3		44
2	The effects of applied and internal strain on the electronic propertiesof amorphous silicon. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , <b>1986</b> , 54, 343-358		43
1	The effects of linear strain on the electronic properties of glow discharge amorphous silicon. Journal of Non-Crystalline Solids, 1985, 77-78, 495-498	3.9	8